ABSTRACT

A nonvolatile ferroelectric memory device stores nonvolatile data in a ferroelectric capacitor and accesses cell data stored in a latch circuit of a sense amplifier in a read operation irrespective of a ferroelectric capacitor. Therefore, the nonvolatile ferroelectric memory cell overcomes the limit of the number of repeated writing operation due to the destroying operation of ferroelectric, and directly access data stored in a latch circuit to access data rapidly. As a result, the present invention obtains a high-speed nonvolatile FeRAM having a high reliability.